

LATCH-BASED PULSE GENERATOR

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BACKGROUND OF THE INVENTION

1. Technical Field

The present invention relates to a pulse generator, and more particularly, to a latch-based pulse generator, which is used in an active matrix type thin film transistor liquid crystal display (TFT-LCD) driver.

2. Discussion of the Related Art

FIG. 1 is a circuit diagram of a common pulse generator 100. Referring to FIG. 1, the pulse generator 100 includes inverters 120 and 140, a flip-flop 110, and a NAND gate 130. As shown in FIG. 1, the inverters 120 and 140 (i.e., complementary metal oxide semiconductor (CMOS) inverters) include positive channel metal oxide semiconductor (PMOS) and negative channel metal oxide semiconductor (NMOS) transistors. The NAND gate 130 also includes two PMOS and NMOS transistors.

The flip-flop 110 latches data *DIN* input to an input terminal *D* and outputs the result of the latching to an output terminal *Q* in response to a clock signal *CLK* input to a clock terminal *CK* and a complementary clock signal *CLKB* input to a complementary clock terminal *CKB*. The flip-flop 110 is reset in response to a falling edge of a reset signal *RSB* input to a reset terminal *RB*.

FIG. 2 is a circuit diagram of the flip-flop 110 shown in FIG. 1. Referring to FIG. 2, the flip-flop 110 includes PMOS transistors 1101, 1105, 1113, and 1117, NMOS transistors 1103, 1107, 1111, and 1115, two inverters 1119 and 1123, and two NAND gates 1109 and 1121.

Referring to FIGS. 1 and 2, the transistors 1101, 1107, 1111, and 1117, the inverter 120, and the NAND gate 130 toggle in response to the clock signal *CLK*, and the transistors 1103, 1105, 1113, and 1115 toggle in response to the complementary clock signal *CLKB*.

FIG. 3 is a circuit diagram of a pulse generator 300 that sequentially latches n data. The pulse generator 300 includes first through n^{th} pulse generators 100_1, 100_2 ... 100_n. The structure of each of the first through n^{th} pulse generators 100_1, 100_2 ... 100_n is the same or similar to that of the pulse generator 100 of FIG. 1.

The pulse generator 100_1 receives and latches an input signal *DIN* in response to a clock signal *CLK* and outputs two output signals *DOUT1* and *L_CLK1*. The output signal *DOUT1* is input to an input terminal *DIN2* of a second pulse generator 100_2 and the other output signal *L_CLK1* is used as a pulse for latching data.

The second pulse generator 100_2 receives and latches the output signal *DOUT1* in response to an inverted clock signal *CLKB* and outputs two output signals *DOUT2* and *L_CLK2*. The output signal *DOUT2* is input to an input terminal of a third pulse generator, and the output signal *L_CLK2* is used as a pulse for latching data.

In the pulse generator 300, the first through n^{th} pulse generators 100_1, 100_2 ... 100_n, are connected in series and generate pulses *L_CLK1*, *L_CLK2* ... *L_CLKn*, respectively, in response to clock signals *CLK* and *CLKB*. Thus, the pulses *L_CLK1*, *L_CLK2* ... *L_CLKn*, which are used to latch related data, are sequentially generated.

For instance, when latching 128 bits of data, a minimum of 128 input clock signals *CLK* or *CLKB* are required. In doing so, each of the pulse generators 100_1, 100_2 ... 100_n, which include the transistors 1101, 1103, 1105, 1107, 1111, 1113, 1115, and 1117, toggle the clock signals *CLK* and *CLKB*. Therefore, the output of one pulse generator (e.g., the pulse generator 100_n) toggles a minimum of 127 times to generate a pulse *L_CLKn*, resulting in excess power consumption.

SUMMARY OF THE INVENTION

The present invention provides a pulse generator capable of generating a pulse with a reduced number of transistors that toggle in response to a clock signal, thereby reducing power consumption.

According to an aspect of the present invention, there is provided a pulse generator comprising a plurality of unit cells, wherein an n^{th} unit cell (n is a natural number more than 2) generates a pulse in response to a divided-by- N clock signal (N is a natural number), a signal output from an $(n-1)^{\text{th}}$ unit cell and a signal output from an $(n+1)^{\text{th}}$ unit cell.

The n^{th} unit cell is reset or generates the pulse whose width is equivalent to the width of the clock signal, based on the logic level of the signal output from the $(n+1)^{\text{th}}$ unit cell. The phases of the signal output from the $(n-1)^{\text{th}}$ unit cell and the signal output from the $(n+1)^{\text{th}}$ unit cell are changed with a time difference.

The n^{th} unit cell comprises a first NAND gate that NANDs the signal output from the $(n-1)^{\text{th}}$ unit cell and the signal output from the $(n+1)^{\text{th}}$ unit cell, a first inverter that inverts a signal output from the first NAND gate, a second NAND gate that NANDs the divided-by- N clock signal and a signal output from the first inverter, a second inverter that inverts a signal output from the second NAND gate and outputs the pulse as an inverted signal, and a latch that latches a reset signal and the signal output from the second NAND gate.

The second NAND gate comprises first and second PMOS transistors, and first and second NMOS transistors, wherein the divided-by- N clock signal is input to a gate of the first PMOS transistor and a gate of the first NMOS transistor, and a signal output from the first inverter is input to a gate of the second PMOS transistor and a gate of the second NMOS transistor.

According to another aspect of the present invention, there is provided a pulse generator comprising a plurality of unit cells, wherein a divided-by- N clock signal (N is a natural number), a signal output from the second output terminal of an $n-1^{\text{th}}$ unit cell (n is a natural number more than 2), and a signal output from a third output terminal of an $n+1^{\text{th}}$ unit cell are input to a first input terminal, a

second input terminal, and a third input terminal of an n^{th} unit cell of the plurality of unit cells, respectively, wherein the n^{th} unit cell outputs a pulse whose width is equivalent to the width of the divided-by-N clock signal to a first output terminal of the n^{th} unit cell in response to the signals that are input to the first, second and
5 third input terminals of the n^{th} unit cell.

The n^{th} unit cell is reset or outputs the pulse whose width is equivalent to the width of the divided-by-N clock signal to the first output terminal of the n^{th} unit cell, based on the logic level of the signal output from the third output terminal of the $(n+1)^{\text{th}}$ unit cell. The phases of the signal output from the second output
10 terminal of the $n-1^{\text{th}}$ unit cell and the signal output from the third output terminal of the $n+1^{\text{th}}$ unit cell are changed with a time difference.

The n^{th} unit cell comprises a first NAND gate that NANDs the signal which is output from the $n-1^{\text{th}}$ unit cell and input to the second input terminal of the n^{th} unit cell, and the signal which is output from the $n+1^{\text{th}}$ unit cell and input to the
15 third input terminal of the n^{th} unit cell; a first inverter that inverts a signal output from the first NAND gate; a second NAND gate that NANDs the divided-by-N clock signal input to the first input terminal of the n^{th} unit cell and a signal output from the first inverter; a second inverter that inverts a signal output from the second NAND gate and outputs an inverted signal as the output signal of the n^{th}
20 unit cell; and a latch that latches a reset signal, and a signal output from the second NAND gate.

The n^{th} unit cell comprises a first NAND gate that NANDs the signal which is output from the $n-1^{\text{th}}$ unit cell and input via the second input terminal of the n^{th} unit cell, and the signal which is output from the $n+1^{\text{th}}$ unit cell and input via the
25 third input terminal of the n^{th} unit cell; a first inverter that inverts a signal output from the first NAND gate; a second NAND gate that NANDs the divided-by-N clock signal input via the first input terminal of the n^{th} unit cell and a signal output from the first inverter; a second inverter that inverts a signal output from the second NAND gate and outputs an inverted signal as an output signal of the n^{th}
30 unit cell; a first transmission circuit that responds to the signal output from the second NAND gate and the signal output from the second inverter; a second

transmission circuit that responds to the signal output from the second NAND gate and the signal output from the second inverter; a third NAND gate that NANDs a reset signal and a signal output from a shared node and outputs the result of NAND to the third output terminal of the n^{th} unit cell; and a third inverter that inverts the signal output from the third NAND gate and outputs an inverted signal to the second output terminal of the n^{th} unit cell.

According to yet another aspect of the present invention, there is provided a pulse generator comprising a first NAND gate that NANDs a first input signal and a second input signal; a first inverter that inverts a signal output from the first NAND gate; a second NAND gate that NANDs a divided-by-N clock signal and a signal output from the first inverter; a second inverter that inverts a signal output from the second NAND gate; and a latch that latches a reset signal and the signal output from the second NAND gate. The second inverter generates a pulse corresponding to the divided-by-N clock signal in response to the second input signal.

According to still another aspect of the present invention, there is provided a pulse generator comprising a first NAND gate that NANDs a first input signal and a second input signal input to a second input terminal; a first inverter that inverts a signal output from the first NAND gate; a second NAND gate that NANDs a divided-by-N clock signal input to a first input terminal and a signal output from the first inverter; a second inverter; a first transmission circuit that responds to a signal output from the second NAND gate and a signal output from the second inverter; a second transmission circuit that responds to the signal output from the second NAND gate and the signal output from the second inverter; a third NAND gate that NANDs a reset signal and a signal output from the shared node and outputs the result of NAND to a third output terminal; and a third inverter. The second inverter generates a pulse whose width is equivalent to the width of the divided-by-N clock signal in response to the second input signal. In addition, the phases of the first and second input signals are changed.

BRIEF DESCRIPTION OF THE DRAWINGS

The above aspects of the present invention will become more apparent by describing in detail exemplary embodiments thereof with reference to the attached drawings, in which:

FIG. 1 is a circuit diagram of a conventional flip-flop-based pulse generator;

FIG. 2 is a circuit diagram of a flip-flop shown in FIG. 1;

FIG. 3 is a circuit diagram of a conventional pulse generator capable of sequentially latching *n* data;

FIG. 4 is a circuit diagram of a latch-based pulse generator according to an exemplary embodiment of the present invention;

FIG. 5 is a circuit diagram of a latch-based pulse generator according to another exemplary embodiment of the present invention;

FIG. 6 is a circuit diagram of a clock signal generating circuit;

FIG. 7 is a circuit diagram of the NAND gates shown in FIGS. 4 and/or 5;

FIG. 8 is a circuit diagram of a pulse generator capable of sequentially latching *n* data; and

FIG. 9 is a timing diagram illustrating the operation of the pulse generator shown in FIG. 8.

DETAILED DESCRIPTION OF EXEMPLARY EMBODIMENTS

FIG. 4 is a circuit diagram of a latch-based pulse generator 400 according to an exemplary embodiment of the present invention. Referring to FIG. 4, the pulse generator 400 includes first, second and third input terminals 481, 482, 483 and first, second and third output terminals 491, 492, 493.

A first NAND gate 401 receives and NANDs an input signal *SFT_IN* input to the second input terminal 482 and an input signal *SFTR_IN* input via the third input terminal 483, and outputs the result of the NAND operation to a first inverter 403.

The level of the input signal *SFTR_IN* input to the third input terminal 483 is changed from a logic high level to a logic low level over a predetermined length

of time after the level of the input signal *SFT_IN* input to the second input terminal 482 is changed from a logic low level to a logic high level.

The first inverter 403 receives and inverts the signal output from the first NAND gate 401 and outputs an inverted signal *enb* to a second NAND gate 405.

5 The second NAND gate 405 receives and NANDs a divided-by-N clock signal *CLK2_EO* (where N is 2) input to the first input terminal 481 and the inverted signal *enb* output from the first inverter 403, and outputs the result of the NAND operation to a second inverter 409 and a NAND gate 411a of a latch 411.

10 The second inverter 409 receives and inverts the signal output from the second NAND gate 405 and outputs an output signal *LAT_PUL* to the first output terminal 491. The output signal *LAT_PUL* is a pulse for latching data.

15 The latch 411 comprises two NAND gates 411a and 411b. The NAND gates 411a and 411b receive and latch a reset signal *SYRB* input via a fourth input terminal 484 and the signal output from the second NAND gate 405 as a set signal, respectively. The latch 411 may be an R-S latch.

A third inverter 413 receives and inverts a signal output from the NAND gate 411a and outputs an output signal *SFTR* to the third output terminal 493. A fourth inverter 415 receives and inverts a signal output from the NAND gate 411b and outputs an output signal *SFT_OUT* to the second output terminal 492.

20 The latch-based pulse generator 400 is reset according to the logic level of the signal *SFTR_IN* input to the third input terminal 483, or receives the divided-by-2 clock signal *CLK2_EO* via the first input terminal 481 and outputs it as an output signal *LAT_PUL* to the first output terminal 491. The latch-based pulse generator 400 is also reset in response to the reset signal *SYRB*.

25 FIG. 5 is a circuit diagram of a latch-based pulse generator 500 according to another exemplary embodiment of the present invention. Referring to FIG. 5, the pulse generator 500 includes first, second and third input terminals 581, 582, 583 and first, second and third output terminals 591, 592, 593.

30 A first NAND gate 501 receives and NANDs an input signal *SFT_IN* from the second input terminal 582 and an input signal *SFTR_IN* from the third input terminal 583, and outputs the result of the NAND operation to a first inverter 503.

The level of the input signal *SFTR_IN* input to the third input terminal 583 is changed from a logic high level to a logic low level over a predetermined length of time after the level of the input signal *SFT_IN* input to the second input terminal 582 is changed from a logic low level to a logic high level.

5 The first inverter 503 receives and inverts a signal output from a first NAND gate 501 and outputs an inverted signal *enb* to a second NAND gate 505 and a second transmission circuit 517.

10 The second NAND gate 505 receives and NANDs a divided-by-2 clock signal *CLK2_EO* input via the first input terminal 581 and the *enb* signal output from the first inverter 503, and outputs the result of the NAND operation to a second inverter 509, a first transmission circuit 511, and the second transmission circuit 517.

15 The first transmission circuit 511 is connected between a shared node 515 and the second output terminal 592, and switches on or off between the shared node 515 and the second output terminal 592 in response to the signal output from an output terminal 507 of the second NAND gate 505 and a signal output from the second inverter 509.

20 The first transmission circuit 511 includes a negative channel metal oxide semiconductor (NMOS) transistor 511a and a positive channel metal oxide semiconductor (PMOS) transistor 511b. The NMOS transistor 511a and the PMOS transistor 511b are connected between the shared node 515 and the second output terminal 592. The signal output from the output terminal 507 of the second NAND gate 505 is input to the gate of the NMOS transistor 511a. The signal output from the second inverter 509 is input to the gate of the PMOS transistor 511b.

25 The second transmission circuit 517 is connected between the shared node 515 and the output terminal of the first inverter 503 and switches on or off between the shared node 515 and the output terminal of the first inverter 503 in response to the signal from the second NAND gate 505 and the signal output from the second inverter 509.

The second transmission circuit 517 includes an NMOS transistor 517b and a PMOS transistor 517a. Both the PMOS transistor 517a and the NMOS transistor 517b are connected between the shared node 515 and the output terminal of the first inverter 503. The signal output from the output terminal 507 of the second NAND gate 505 is input to the gate of the PMOS transistor 517a. A signal output from the second inverter 509 is input to the gate of the NMOS transistor 517b.

The second inverter 509 receives and inverts the signal output from the second NAND gate 505 and outputs an output signal *LAT_PUL* to the first output terminal 591. The output signal *LAT_PUL* is a pulse for latching data.

A third NAND gate 521 receives and NANDs a reset signal *SYRB* input via a fourth input terminal 584 and the signal output from the shared node 515, and outputs a signal *SFTR* as the result of the NAND operation to the third output terminal 593 and a third inverter 523.

The third inverter 523 receives and inverts the signal output from the third NAND gate 521 and outputs an inverted signal *SFT_OUT* to the second output terminal 592 and the first transmission circuit 511.

FIG. 6 is a circuit diagram of a clock signal generating circuit 600.

Referring to FIG. 6, the clock signal generating circuit 600, which generates a divided-by-2 clock signal, includes a flip-flop 610, a first NOR gate 630, and a second NOR gate 650.

A clock signal *CLK* is input to a clock terminal *CK* of the flip-flop 610, an inverted clock signal *CLKB* is input to an inverted clock terminal *CKB* of the flip-flop 610, and a signal output from an inverted output terminal *QB* of the flip-flop 610 is input to an input terminal *D* of the flip-flop 610. The clock signal *CLK* and the inverted clock signal *CLKB* are complementary to each other, and an output signal *CLK2* and an inverted output signal *CLK2B* are complementary to each other.

The first NOR gate 630 receives and NORs the clock signal *CLK* and the output signal *CLK2* output from the flip-flop 610, and outputs a signal *CLK2_ODD*

as the result of the NOR operation. The output signal *CLK2* output from the flip-flop 610 is a divided-by-2 signal of the clock signal *CLK*.

The second NOR gate 650 receives and NORs the clock signal *CLK* and the inverted output signal *CLK2B* output from the flip-flop 610, and outputs a signal *CLK2_EVEN* as the result of the NOR operation. The inverted output signal *CLK2B* is a divided-by-2 signal of the inverted clock signal *CLKB*. The flip-flop 610 is reset in response to a falling edge of a reset signal *RESETB*.

The waveforms of the signal *CLK2_ODD* output from the first NOR gate 630 and the signal *CLK2_EVEN* output from the second NOR gate 650 are illustrated in FIG. 9. The divided-by-2 clock signals *CLK2_EO* shown in FIGS. 4 and 5 are equivalent or similar to the signal *CLK2_ODD* output from the first NOR gate 630 or the signal *CLK2_EVEN* output from the second NOR gate 650. Thus, the signal *CLK2_ODD* is a divided-by-2 odd-numbered clock signal and the signal *CLK2_EVEN* is a divided-by-2 even-numbered clock signal.

FIG. 7 is a circuit diagram of the NAND gates 405, 505 shown in FIGS. 4 and 5. Referring to FIG. 7, a first PMOS transistor 4051 and a second PMOS transistor 4053 are connected in parallel between a power supply voltage *VDD* and the output terminals 407, 507 of FIGS. 4 and 5 of the second NAND gates 405, 505. A first NMOS transistor 4055 and a second NMOS transistor 4057 are connected in series between the output terminals 407, 507 of the second NAND gates 405, 505 and a ground voltage *VSS*.

The divided-by-2 clock signal *CLK2_EO* is input to the gate of the first PMOS transistor 4051 and the gate of the first NMOS transistor 4055. A signal *enb* output from the first inverters 403, 503 of FIGS. 4 and 5 is input to the gate of the second PMOS transistor 4053 and the gate of the second NMOS transistor 4057.

Because the divided-by-2 clock signal *CLK2_EO* is input to the gate of the first PMOS transistor 4051 and the gate of the first NMOS transistor 4055, only the first PMOS transistor 4051 and the first NMOS transistor 4055 toggle in response to the divided-by-2 clock signal *CLK2_EO*.

On the other hand, in the conventional pulse generator 100 shown in FIGS. 1 and 2, the transistors 1101, 1103, 1105, 1107, 1111, 1113, 1115, and 1117, the transistors of the inverter 120, and the transistors of the NAND gate 130 all toggle in response to the clock signal *CLK*. Therefore, the power consumed by the pulse generators 400, 500 of FIGS. 4 and 5 with the NAND gates 405, 505, shown in FIG. 7 is significantly smaller than the power consumed by the pulse generator 100 shown in FIG. 1.

FIG. 8 is a circuit diagram of a pulse generator 800 capable of sequentially latching *n* data. Referring to FIG. 8, the pulse generator 800 includes a first dummy unit cell 810, a pulse generator set 830, and a second dummy unit cell 850.

The pulse generator set 830 includes *n* unit cells 830_1, 830_2 ... 830_*n*. Each of the *n* unit cells 830_1, 830_2 ... 830_*n* has the same or similar construction and function as the pulse generator 400, 500 of FIGS. 4 and 5. The *n*th unit cell 830_1 outputs the divided-by-2 odd-numbered clock signal *CLK2_ODD* as an output signal *LAT_PUL1* in response to the divided-by-2 odd-numbered clock signal *CLK2_ODD*, an output signal *SFT_OUT0* output from the (*n*-1)th (i.e., first dummy) unit cell 810, and an output signal *SFTR2* output from the *n*+1th unit cell 830_2.

More specifically, the *n*th unit cell 830_1 is reset in response to the logic level of the signal *SFTR2* output from the (*n*+1)th unit cell 830_2, or outputs an output signal *LAT_PUL* as a pulse whose width is equivalent to the width of the divided-by-2 odd-numbered clock signal *CLK2_ODD*. The pulse *LAT_PUL* is used to latch data input to a source data line of for example, an active matrix type thin film transistor liquid crystal display (TFT_LCD) driver.

Thus, when the inverted output signal *enb* output from the first inverters 403, 503 of FIGS. 4 and 5 is at a logic low level, the pulse generators 400, 500 output a deactivated output signal *LAT_PUL*, i.e., *LAT_PUL* is at a logic low level, irrespective of the level of the divided-by-2 clock signal *CLK2_EO*. However, when the output signal *enb* output from the first inverters 403, 503 is at a logic

high level, the pulse generators 400, 500 output as the output signal *LAT_PUL* a pulse whose width is equivalent to the width of the clock signal *CLK2_EO*.

In the unit cell 830_1, the divided-by-2 clock signal *CLK2_ODD* is input to its first input terminal, a signal *SFT_OUT0* output from a second output terminal of the first dummy unit cell 810 is input to its second input terminal, and a signal *SFTR2* output from a third output terminal of the unit cell 830_2 is input to its third input terminal.

In the n^{th} unit cell 803_n, the divided-by-2 odd-numbered clock signal *CLK2_ODD* is input to its first input terminal, a signal output from a second output terminal of the $(n-1)^{\text{th}}$ unit cell is input to its second input terminal, and a signal *SFTRD2* output from a third output terminal of the second dummy unit cell 850 is input to its third input terminal. A signal *LAT_PULn* output from a first output terminal of the n^{th} unit cell 830_n is used as a signal for latching n^{th} data.

FIG. 9 is a timing diagram illustrating the operation of the pulse generator 800, shown in FIG. 8. The operation of the pulse generator 800 will be described in detail with reference to FIGS. 4-9.

First, a case where 128 data bits are sequentially latched is explained. The clock signal generating circuit 600 of FIG. 6 alternately generates the divided-by-2 odd-numbered clock signal *CLK2_ODD* and the divided-by-2 even-numbered clock signal *CLK2_EVEN* in response to the clock signal *CLK* and the inverted clock signal *CLKB*.

The first dummy unit cell 810 outputs an activated signal *SFT_OUT0* as an input signal *SFT_IN1* to the unit cell 830_1 when the start signal *START* input as an input signal *SFT_IN0* to the second input terminal of the first dummy unit cell 810 is activated and an activated signal *SFTR1* output from a third output terminal of the activated unit cell 830_1 is input as an input signal *SFTR_IND1* to the third input terminal of the first dummy unit cell 810.

The unit cell 830_1 generates the pulse *LAT_PUL1* whose width is equivalent to the width of the divided-by-2 odd-numbered clock signal *CLK2_ODD* in response to the activated input signal *SFT_IN1* and the output signal *SFTR2* output from the unit cell 830_2, and outputs an activated output

signal *SFT_OUT1* and the deactivated output signal *SFTR1*, respectively.

Accordingly, the first dummy unit cell 810 is reset in response to the deactivated output signal *SFTR1*.

5 The activated signal *SFT_OUT1* output from the unit cell 830_1 is input as
an input signal *SFT_IN2* to the unit cell 830_2. The unit cell 830_2 generates a
pulse *LAT_PUL2* whose width is equivalent to the width of a divided-by-2
even-numbered clock signal *CLK2_EVEN* in response to the activated input
signal *SFT_IN2* and an activated output signal *SFTR3* output from a third unit cell,
and activates and outputs an activated output signal *SFT_OUT2* and the
10 deactivated output signal *SFTR2*. The unit cell 830_1 is reset in response to the
deactivated output signal *SFTR2*.

The above operations of the pulse generator 800 are repeated until 128
source data bits are latched. Therefore, 128 pulses are sequentially generated
by each of 128 unit cells 830_1, 830_2 ... 830_n.

15 While this invention has been particularly shown and described with
reference to exemplary embodiments thereof, it will be understood by those
skilled in the art that various changes in form and details may be made therein
without departing from the spirit and scope of the invention as defined by the
appended claims and their equivalents.

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